

## VCRR N-Channel Super Trench Power MOSFET

### Description

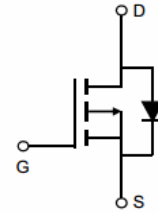
The VCRRP50P80 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### General Features

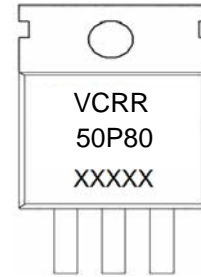
- $V_{DS} = -50V, I_D = -80A$   
 $R_{DS(ON)} = 7.6m\Omega$  (typical) @  $V_{GS} = -10V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

### Application

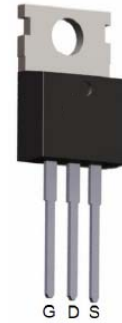
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Schematic Diagram



Marking and pin assignment



TO-220-3L top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package
VCRRP50P80		TO-220-3L

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-50	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-80	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	-56	A
Pulsed Drain Current	$I_{DM}$	-320	A
Maximum Power Dissipation	$P_D$	180	W
Derating factor		1.2	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	1024	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	0.83	$^\circ C/W$
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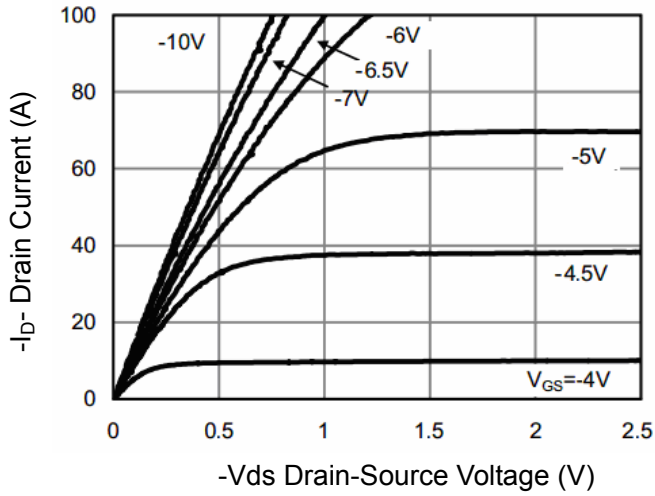
### Electrical Characteristics ( $T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-50		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-50V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.5	-2.5	-3.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-40A$	-	7.6	9	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=-5V, I_D=-40A$	-	35	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{iss}$	$V_{DS}=-25V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	3550	-	PF
Output Capacitance	$C_{oss}$		-	1155	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	22	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-25V, I_D=-40A$ $V_{GS}=-10V, R_G=1.6\Omega$	-	12.5	-	nS
Turn-on Rise Time	$t_r$		-	10	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	35	-	nS
Turn-Off Fall Time	$t_f$		-	8	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=-25V, I_D=-40A,$ $V_{GS}=-10V$	-	38.5	-	nC
Gate-Source Charge	$Q_{gs}$		-	11.2	-	nC
Gate-Drain Charge	$Q_{gd}$		-	7.5	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=-40A$	-		-1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	-80	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}\text{C}, I_F = -40A$ $di/dt = 100A/\mu s$ (Note 3)	-	30	-	nS
Reverse Recovery Charge	$Q_{rr}$		-	75	-	nC

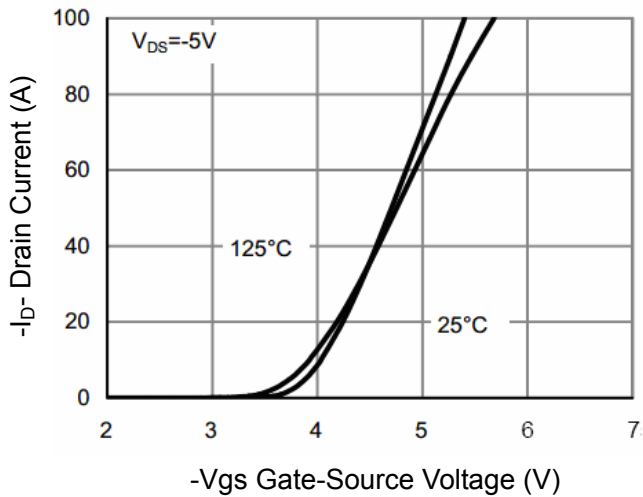
#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_J=25^{\circ}\text{C}, V_{DD}=-25V, V_G=-10V, L=0.5\text{mH}, R_G=25\Omega$

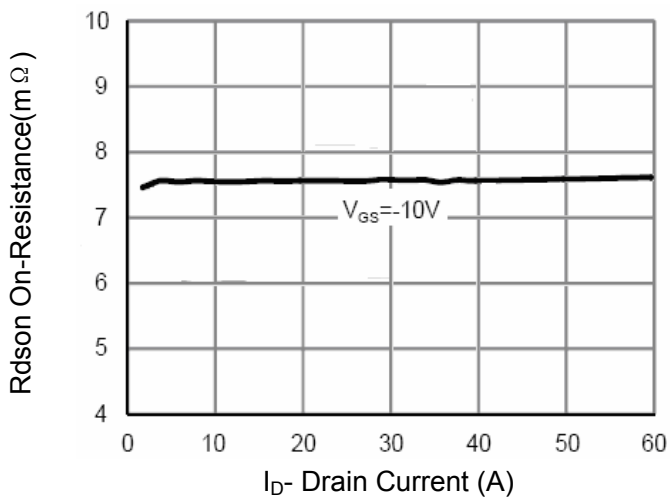
**Typical Electrical and Thermal Characteristics**



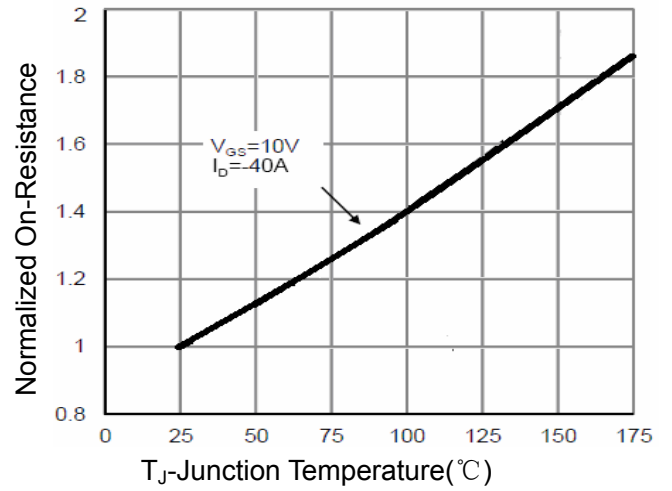
**Figure 1 Output Characteristics**



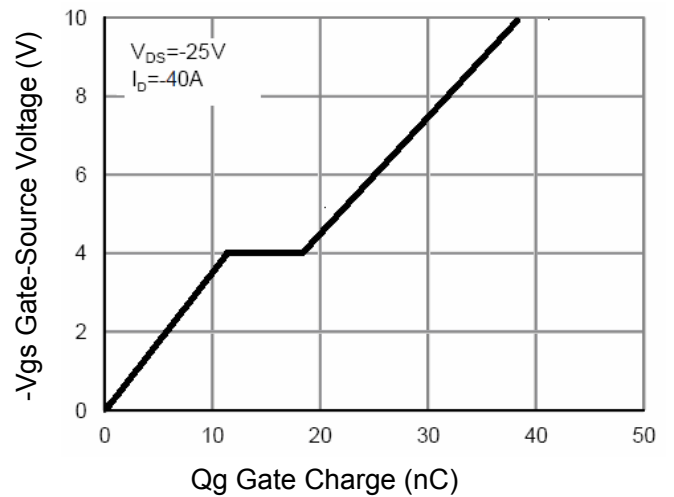
**Figure 2 Transfer Characteristics**



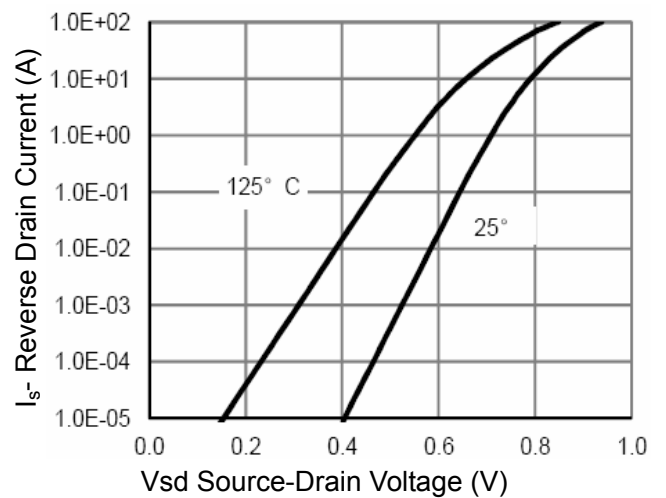
**Figure 3 Rdson- Drain Current**



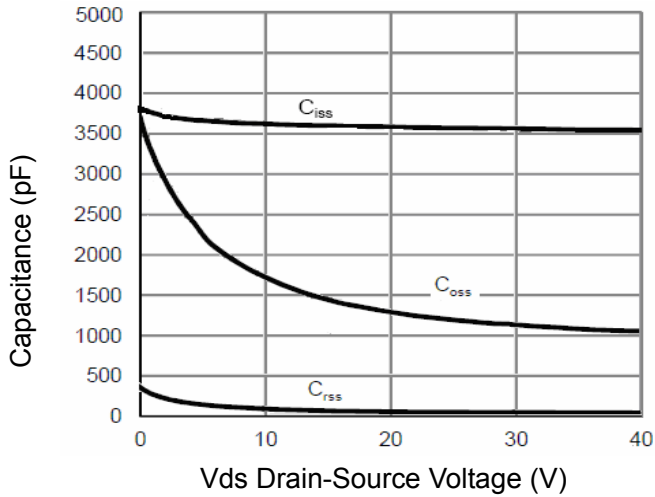
**Figure 4 Rdson-Junction Temperature**



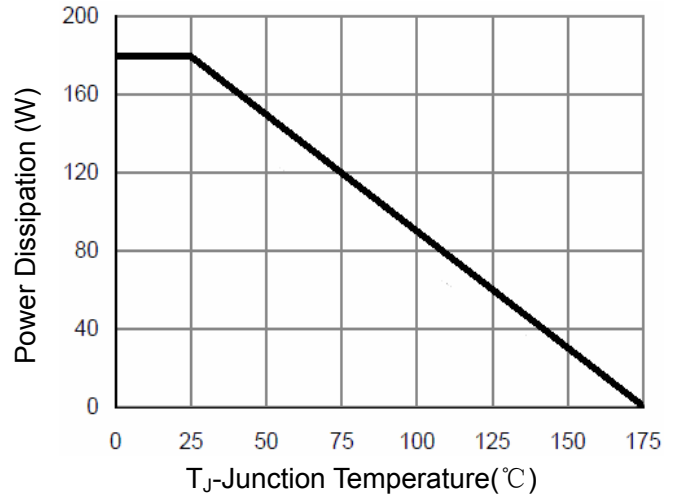
**Figure 5 Gate Charge**



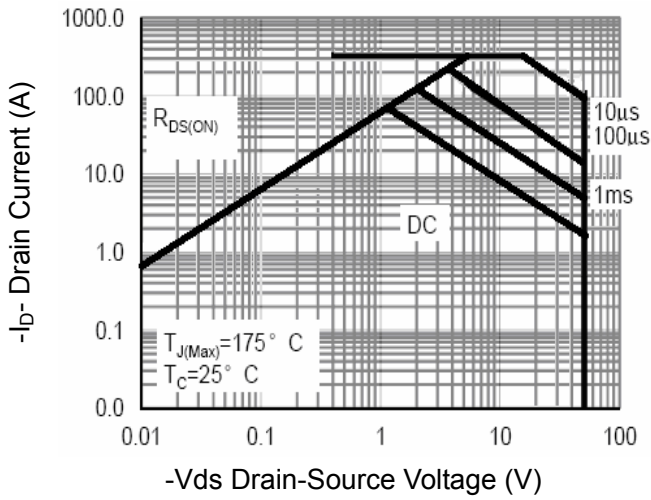
**Figure 6 Source- Drain Diode Forward**



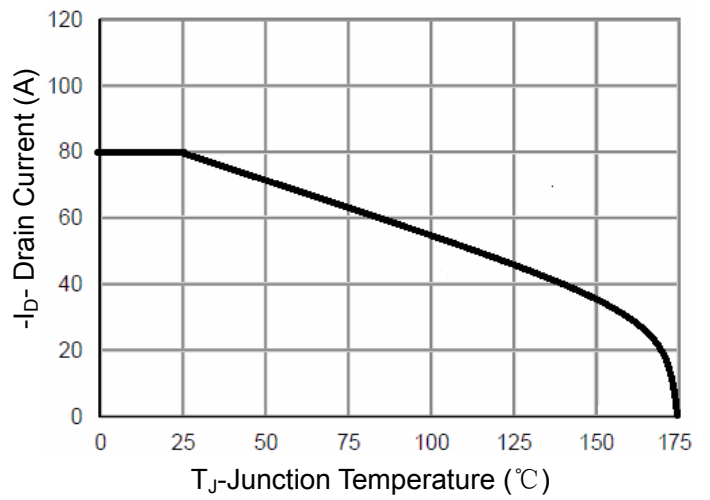
**Figure 7 Capacitance vs Vds**



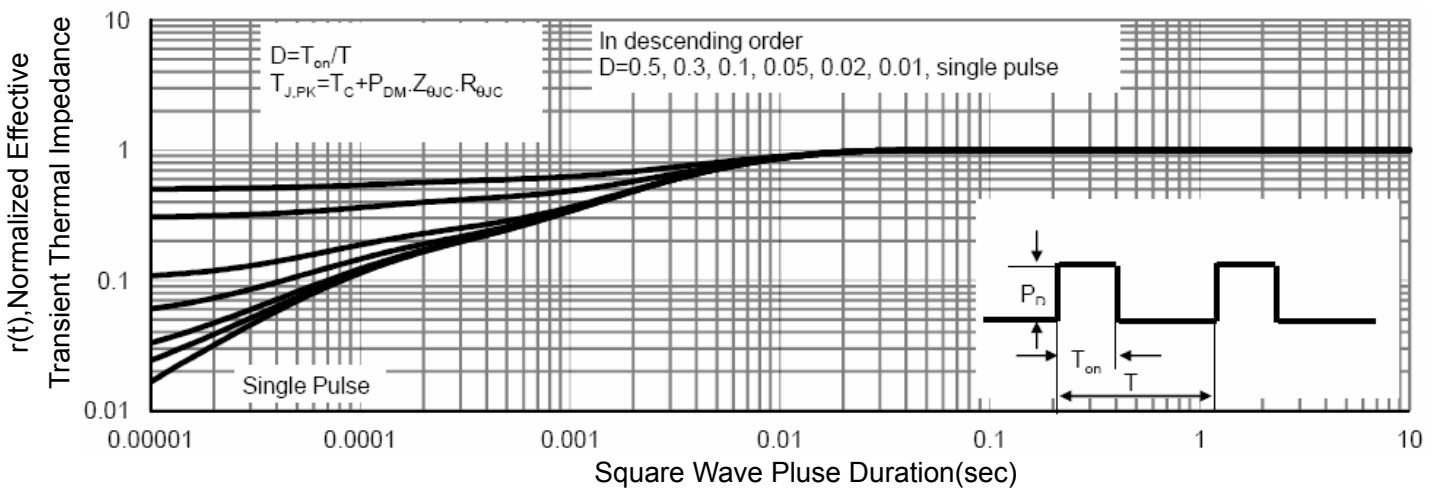
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area**

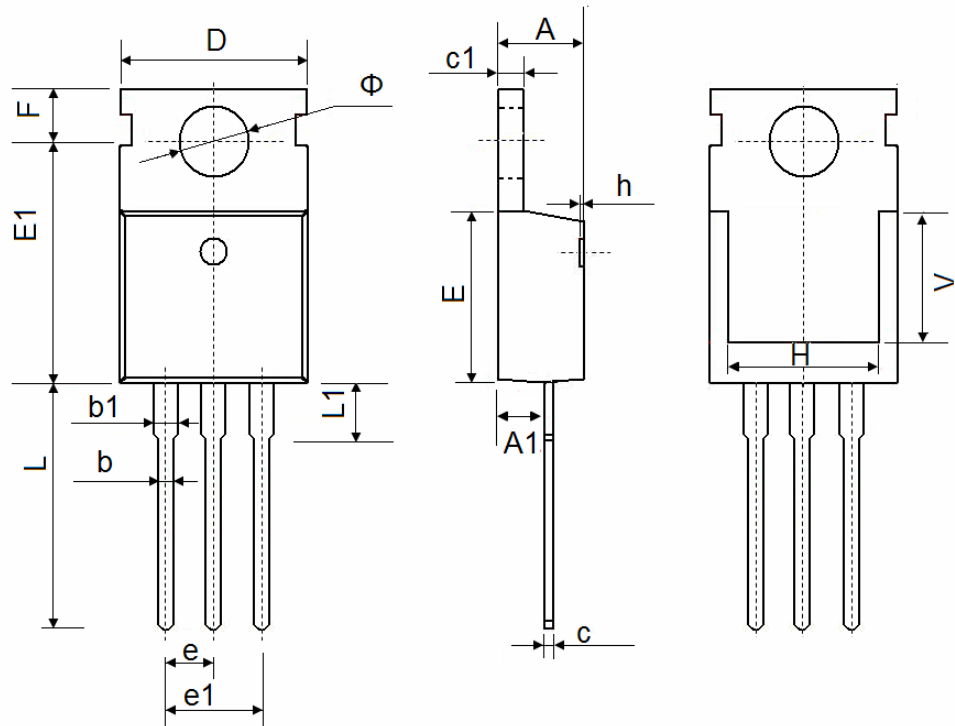


**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

**TO-220-3L Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

### **Attention**

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